BMS3003

P-Channel Power MOSFET -60V, -78A, 6.5mΩ, TO-220F-3SG



Features

- · ON-resistance RDS(on)1=5.0m Ω (typ.)
- · Input capacitance Ciss=13200pF (typ.)
- · -4V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

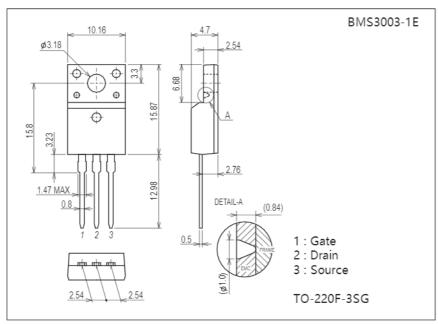
Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		-60	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-78	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-312	А
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		420	mJ
Avalanche Current *2	IAV		-60	А

Note :*1 V_{DD} =-36V, L=100 μ H, IAV=-60A (Fig.1)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Package Dimensions

unit: mm (typ.) 7529-001



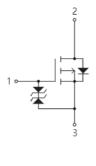
Product & Package Information

Package : TO-220F-3SGJEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./tube

Marking Electrical Connection





ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

^{*2} L≤100μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Onit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-60V, V _{GS} =0V			-10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA -1.2			-2.6	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-39A		130		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	ID=-39A, VGS=-10V		5.0	6.5	mΩ
	RDS(on)2	ID=-39A, VGS=-4V		6.5	9.0	mΩ
Input Capacitance	Ciss			13200		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		1300		pF
Reverse Transfer Capacitance	Crss			950		pF
Turn-ON Delay Time	t _d (on)			90		ns
Rise Time	t _r	S Fi- 3		360		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		1200		ns
Fall Time	tf			680		ns
Total Gate Charge	Qg			285		nC
Gate to Source Charge	Qgs	VDS=-36V, VGS=-10V, ID=-78A		35		nC
Gate to Drain 'Miller' Charge	Qgd			70		nC
Diode Forward Voltage	V _{SD}	IS=-78A, VGS=0V		-0.95	-1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		150		ns
Reverse Recovery Charge	Qrr	IS=-78A, VGS=0V, di/dt=-100A/μs		470		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig.1 Unclamped Inductive Switching Test Circuit

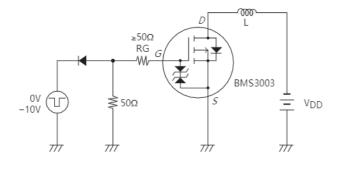


Fig.3 Reverse Recovery Time Test Circuit

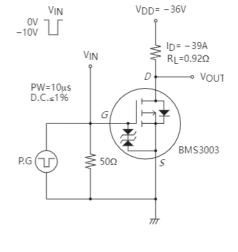
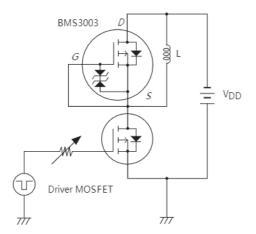
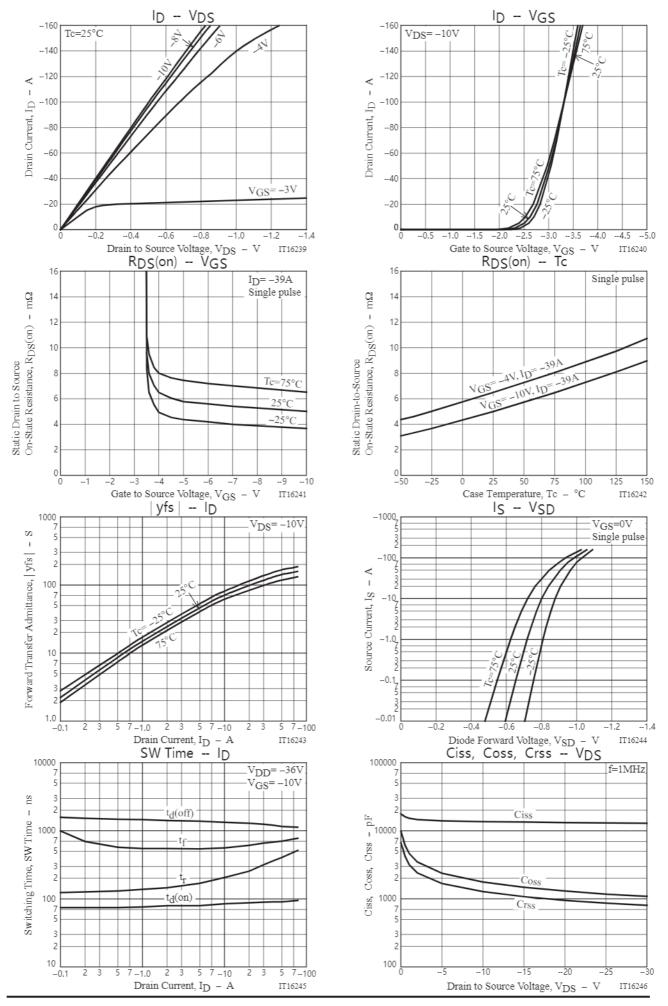


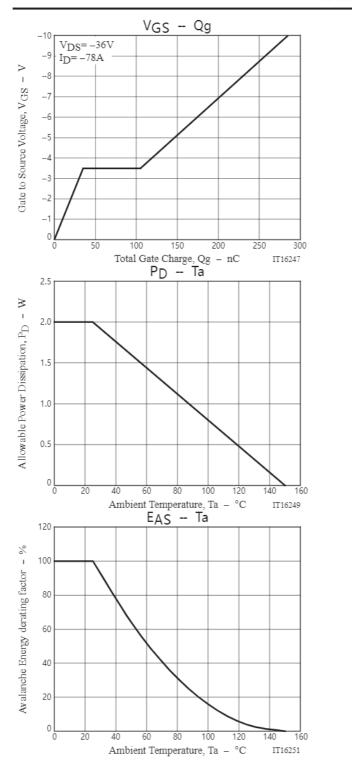
Fig.2 Switching Time Test Circuit

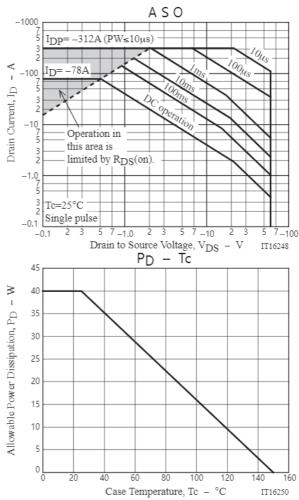


Ordering Information

Device	Package	Shipping	memo	
BMS3003-1E	TO-220F-3SG	50pcs./tube	Pb Free	

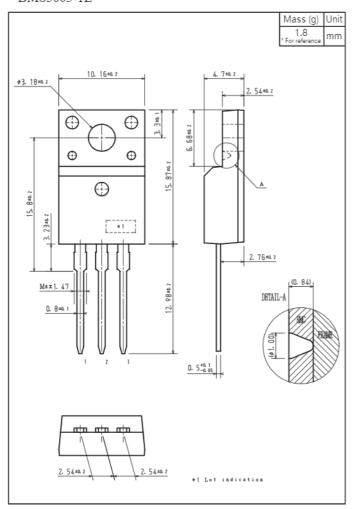






Outline Drawing

BMS3003-1E



Note on usage: Since the BMS3003 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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